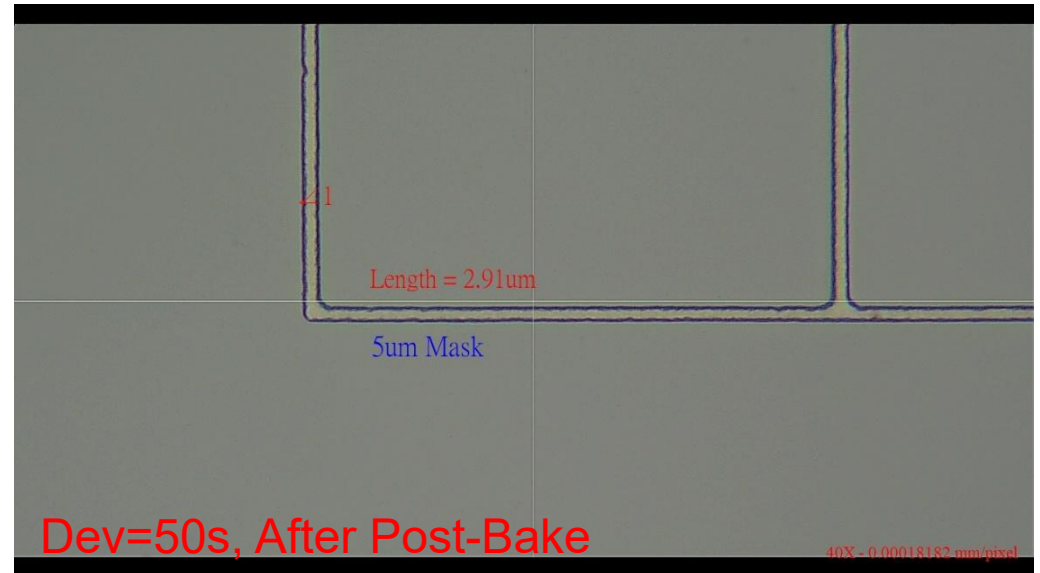
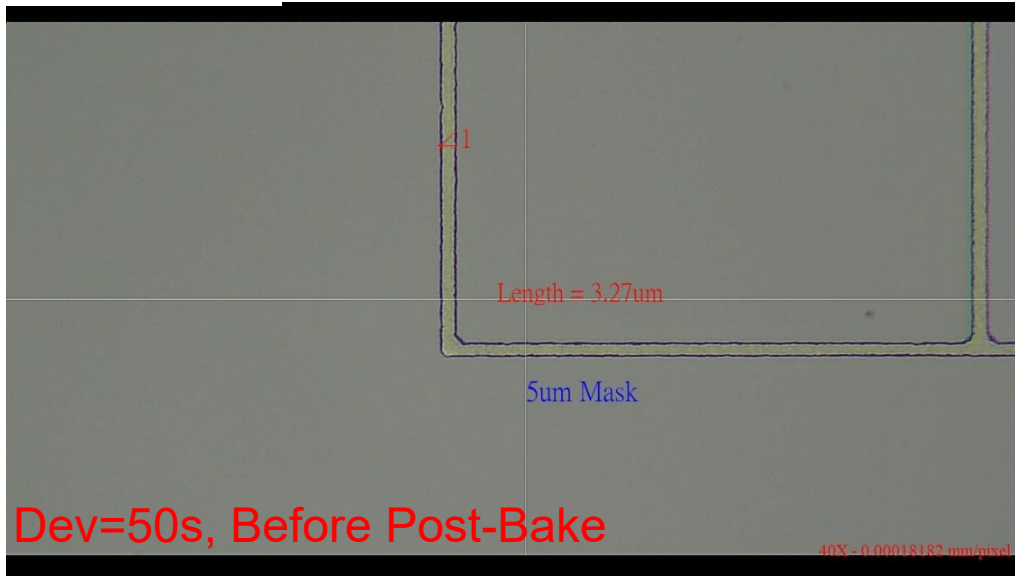


Ultra High Resolution Black Resist SEBK-131

Product	Vis. (cps)	S.C. (%)	OD (μm^{-1})	BT (sec)	Dev. Time (sec)	Adhesion (μm)	THK after PB (@550rpm) (μm)	OD
131	4.0	23.5	4.0	25	40	3	1.1	4.37

Process Parameter	
Spin Speed	550 rpm on 0.5mm EXG
THK	Control at 1.25 μm before Post-bake
Pre-bake	100°C*2.5min, directly
Power	200mJ/ cm^2 & Gap=15 μm @25mW
Dev.	40~45 sec in 1:99 SEDR-5 / 0.15MPa & 25 °C
Rinse	20sec/ 0.15MPa & 25 °C
HPMJ	10sec/ 0.4MPa & 25 °C
Post-bake	200 °C*30min clean oven

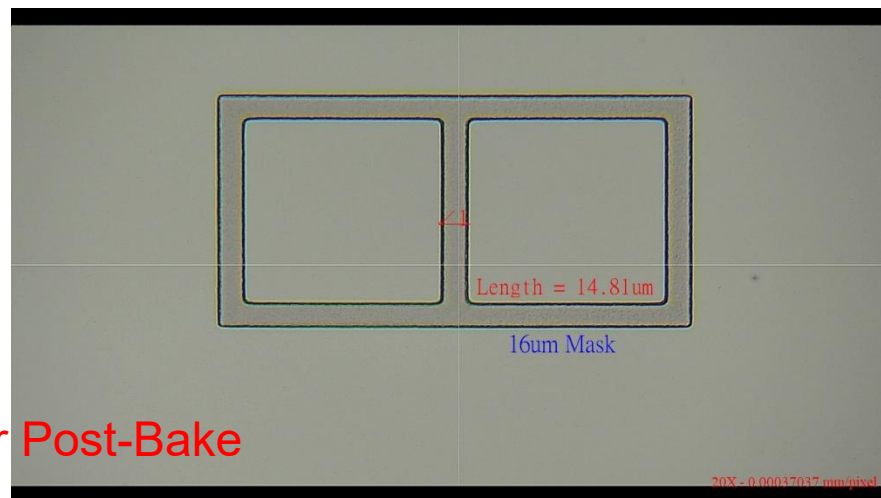
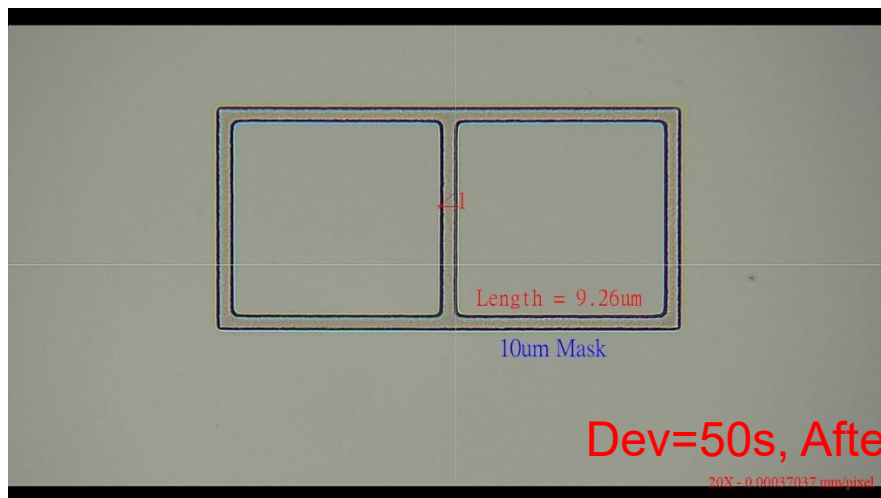
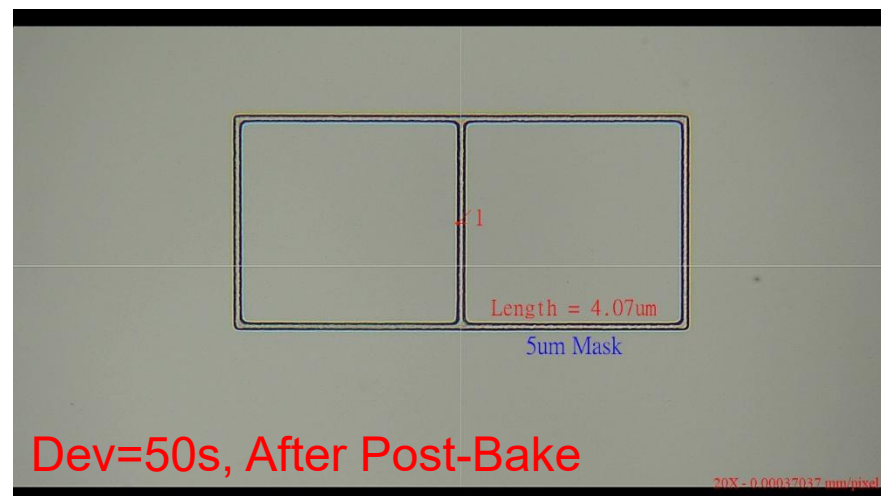
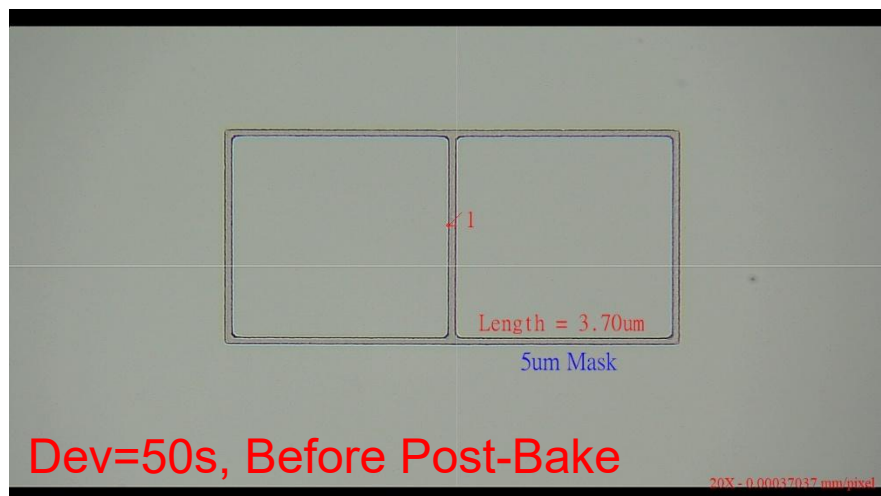
3 μ m Pattern OM



THK=1.1 μ m, Exp. Dose=200mJ/cm², Gap=15 μ m, Postbake=200 $^{\circ}$ C *30min

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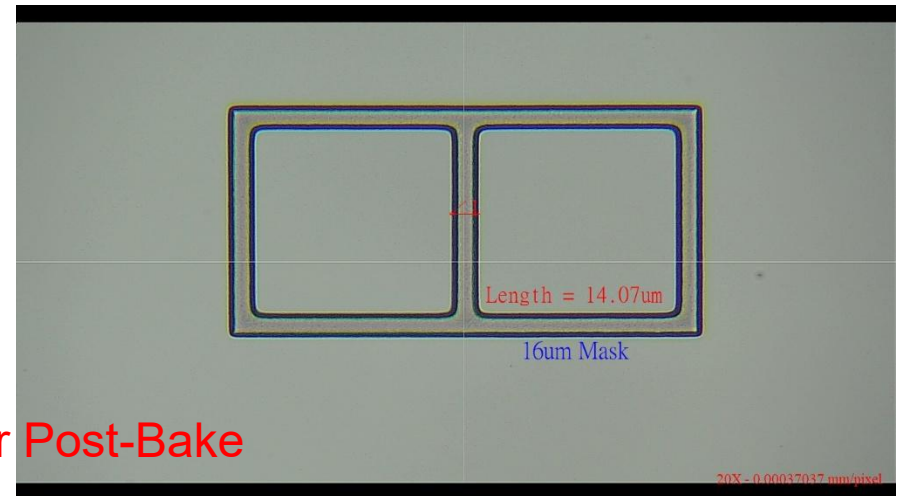
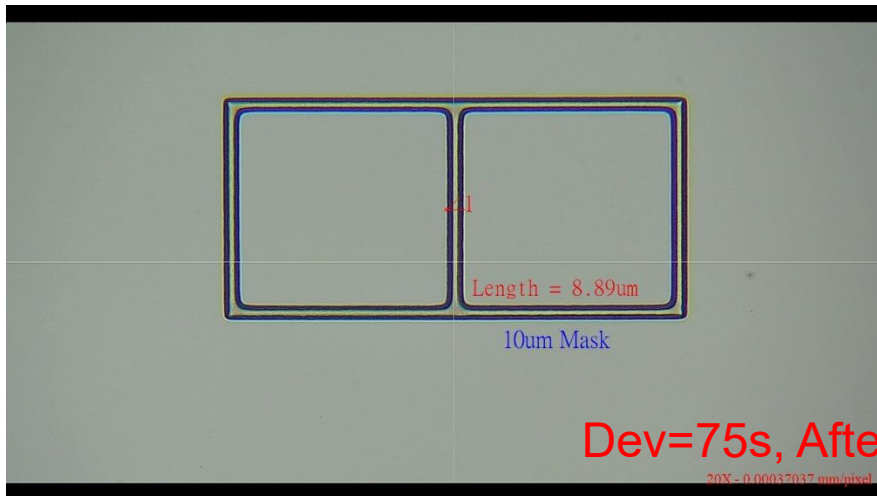
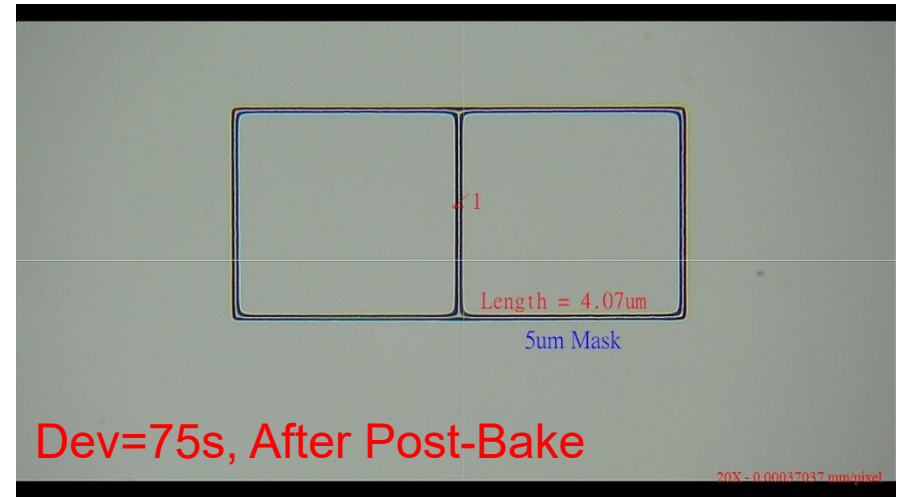
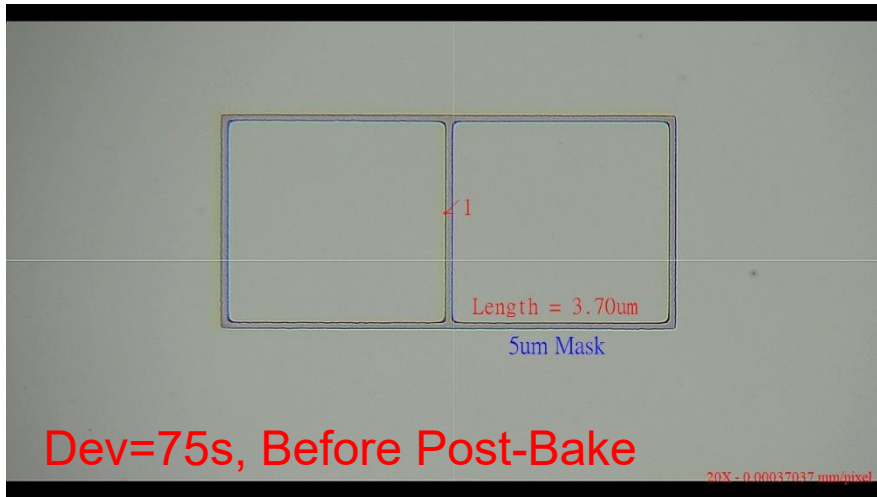
THK=1.25 μ m Pattern OM



THK=1.25 μ m/ OD>4.8, Exp. Dose=300mJ/cm², Gap=15 μ m, Postbake=200 $^{\circ}$ C *30min

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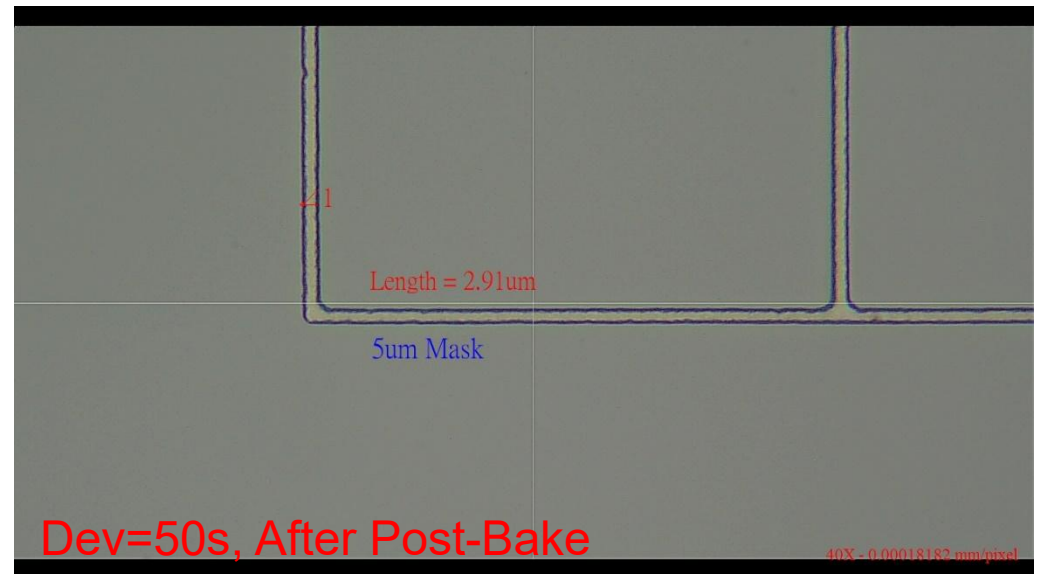
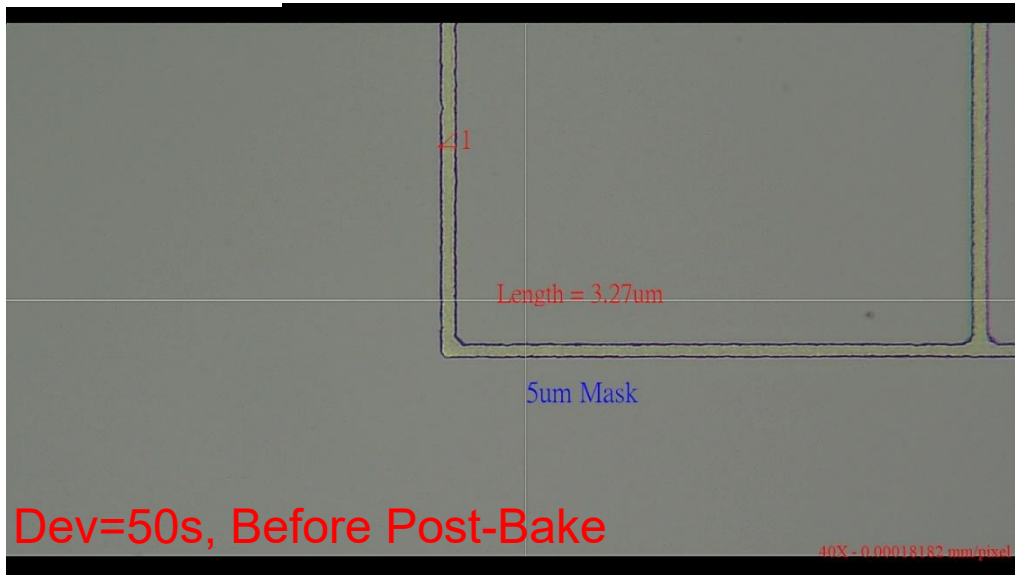
THK=2.1 μ m Pattern OM



THK=2.1 μ m / OD>6.0, Exp. Dose=500mJ/cm², Gap=15 μ m, Postbake=200 $^{\circ}$ C *30min

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3 μ m Pattern OM



THK=1.1 μ m, Exp. Dose=200mJ/cm², Gap=15 μ m, Postbake=200 $^{\circ}$ C *30min

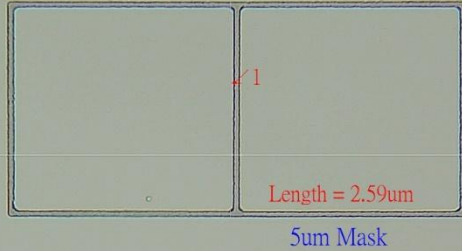
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Ultra High Resolution Black Resist SEBK-131B

Product	Vis. (cps)	S.C. (%)	OD (μm^{-1})	BT (sec)	Dev. Time (sec)	Adhesion (μm)	THK after PB (@550rpm) (μm)	OD
131B	4.0	23.5	4.0	20	35	2	1.02	4.04

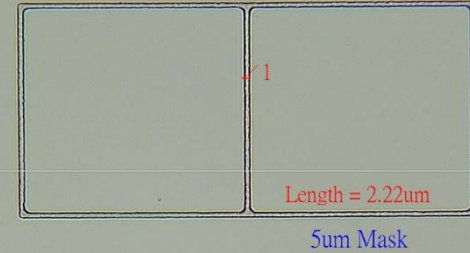
Process Parameter	
Spin Speed	550 rpm on 0.5mm EXG
THK	Control at 1.25 μm before Post-bake
Pre-bake	100°C*2.5min, directly
Power	400mJ/ cm^2 & Gap=15 μm @25mW
Dev.	40sec in 1:99 SEDR-5 / 0.15MPa & 25 °C
Rinse	20sec/ 0.15MPa & 25 °C
HPMJ	10sec/ 0.4MPa & 25 °C
Post-bake	200 °C*30min clean oven

2.5 μ m Pattern OM@400mJ/ cm²



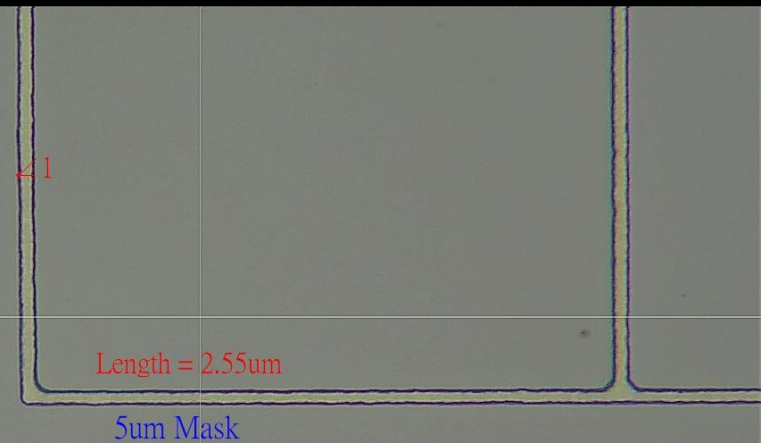
Dev=40s, Before Post-Bake

20X - 0.00037037 mm/pixel



Dev=40s, After Post-Bake

20X - 0.00037037 mm/pixel



Dev=40s, After Post-Bake

40X - 0.00018182 mm/pixel

THK=1.0 μ m, Exp. Dose=400mJ/cm², Gap=15 μ m, Postbake=200 $^{\circ}$ C *30min

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